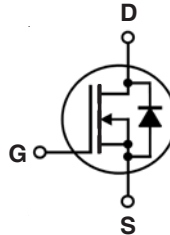


## Depletion Mode MOSFET

**IXTY1R6N50D2**  
**IXTA1R6N50D2**  
**IXTP1R6N50D2**

$V_{DSX} = 500V$   
 $I_{D(on)} \geq 1.6A$   
 $R_{DS(on)} \leq 2.3\Omega$

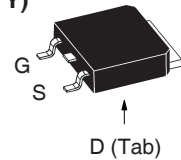
### N-Channel



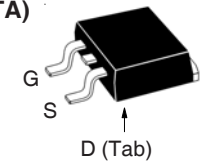
Symbol	Test Conditions	Maximum Ratings	
$V_{DSX}$	$T_J = 25^\circ C$ to $150^\circ C$	500	V
$V_{GSX}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$P_D$	$T_C = 25^\circ C$	100	W
$T_J$		- 55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		- 55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-252	0.35	g
	TO-263	2.50	g
	TO-220	3.00	g

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSX}$	$V_{GS} = -5V, I_D = 250\mu A$	500		V
$V_{GS(off)}$	$V_{DS} = 25V, I_D = 100\mu A$	- 2.5		- 4.5 V
$I_{GSX}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$ nA
$I_{DSX(off)}$	$V_{DS} = V_{DSX}, V_{GS} = -5V$ $T_J = 125^\circ C$			2 $\mu A$ 25 $\mu A$
$R_{DS(on)}$	$V_{GS} = 0V, I_D = 0.8A$ , Note 1			2.3 $\Omega$
$I_{D(on)}$	$V_{GS} = 0V, V_{DS} = 25V$ , Note 1	1.6		A

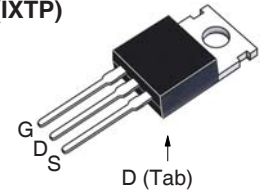
TO-252 (IXTY)



TO-263 (IXTA)



TO-220 (IXTP)



G = Gate      D = Drain  
S = Source     Tab = Drain

### Features

- Normally ON Mode
- International Standard Packages
- Molding Epoxies Meet UL94 V-0 Flammability Classification

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- Audio Amplifiers
- Start-up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 30\text{V}, I_D = 0.8\text{A}$ , Note 1	1.00	1.75	S
$C_{iss}$	$V_{GS} = -10\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		645	pF
$C_{oss}$			65	pF
$C_{rss}$			16.5	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = \pm 5\text{V}, V_{DS} = 250\text{V}, I_D = 0.8\text{A}$ $R_G = 5\Omega$ (External)		25	ns
$t_r$			70	ns
$t_{d(off)}$			35	ns
$t_f$			41	ns
$Q_{g(on)}$	$V_{GS} = 5\text{V}, V_{DS} = 250\text{V}, I_D = 0.8\text{A}$		23.7	nC
$Q_{gs}$			2.2	nC
$Q_{gd}$			13.8	nC
$R_{thJC}$	TO-220			1.25 $^\circ\text{C/W}$
$R_{thCS}$			0.50	$^\circ\text{C/W}$

**Safe-Operating-Area Specification**

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 400\text{V}, I_D = 0.15\text{A}, T_C = 75^\circ\text{C}, T_p = 5\text{s}$	60		W

**Source-Drain Diode**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{SD}$	$I_F = 1.6\text{A}, V_{GS} = -10\text{V}$ , Note 1		0.8	1.3 V
$t_{rr}$	$I_F = 1.6\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = -10\text{V}$		400	ns
$I_{RM}$			9.16	A
$Q_{RM}$			1.83	$\mu\text{C}$

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

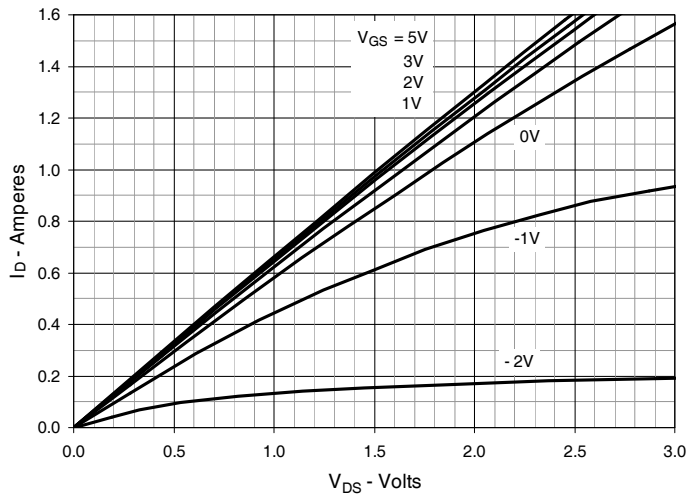


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

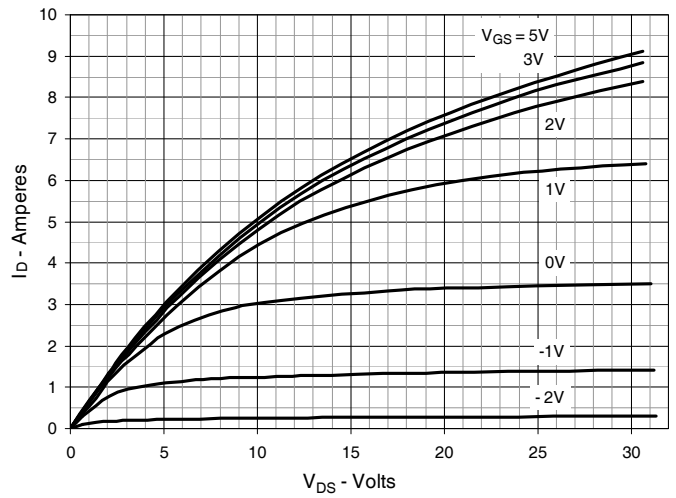


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

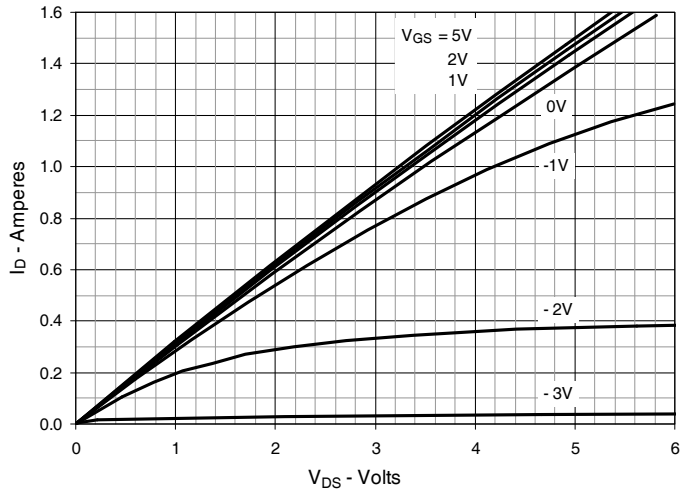


Fig. 4. Drain Current @  $T_J = 25^\circ\text{C}$

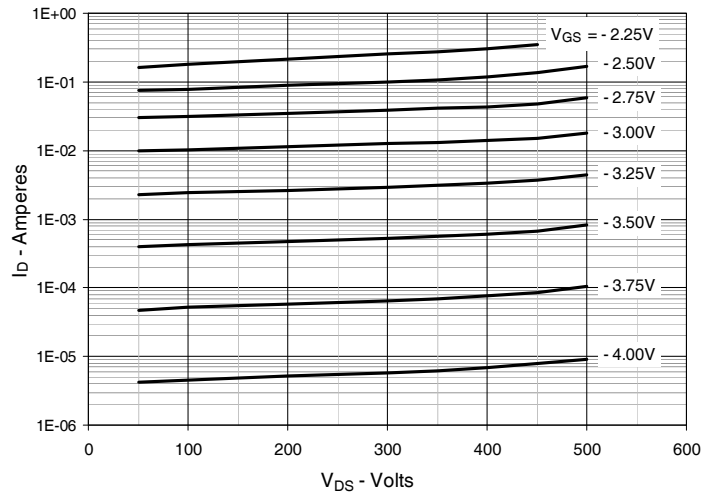


Fig. 5. Drain Current @  $T_J = 100^\circ\text{C}$

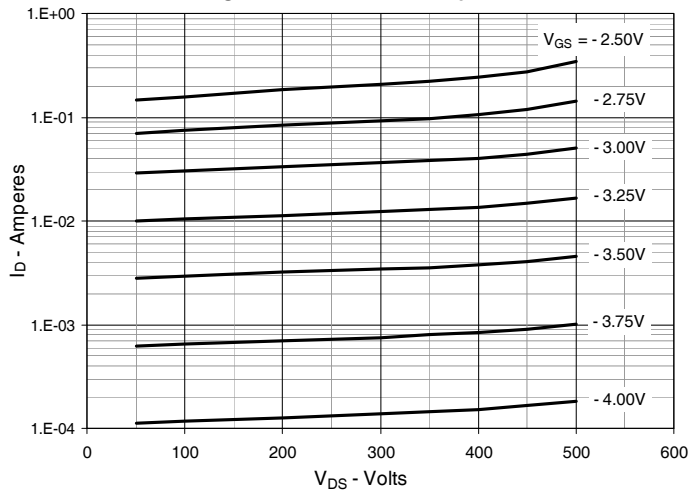


Fig. 6. Dynamic Resistance vs. Gate Voltage

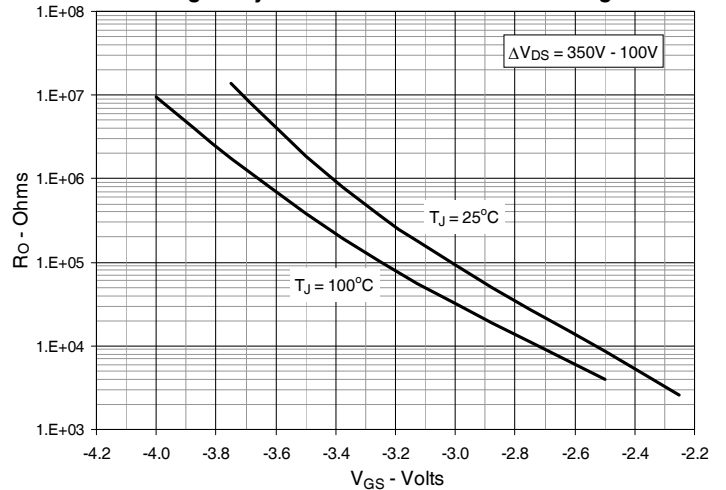


Fig. 7. Normalized  $R_{DS(on)}$  vs. Junction Temperature

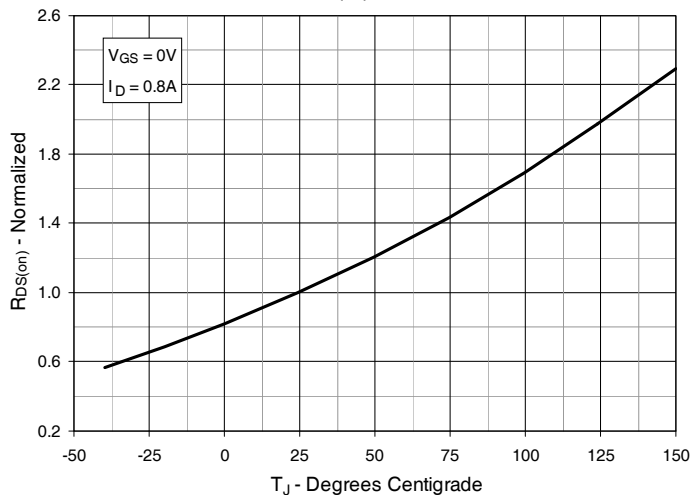


Fig. 8.  $R_{DS(on)}$  Normalized to  $I_D = 0.8A$  Value vs. Drain Current

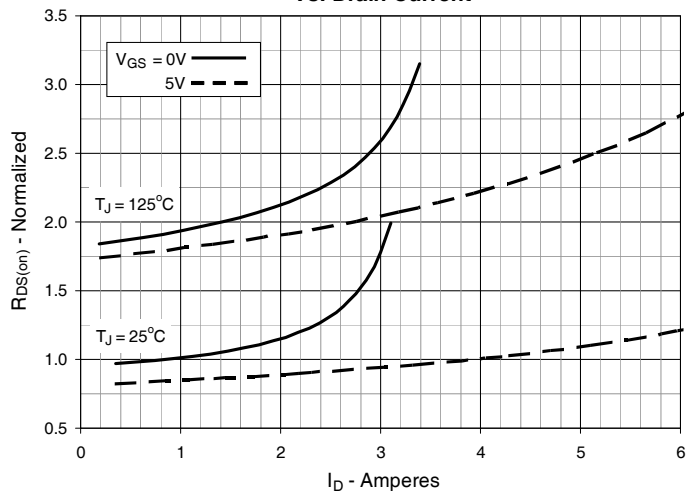


Fig. 9. Input Admittance

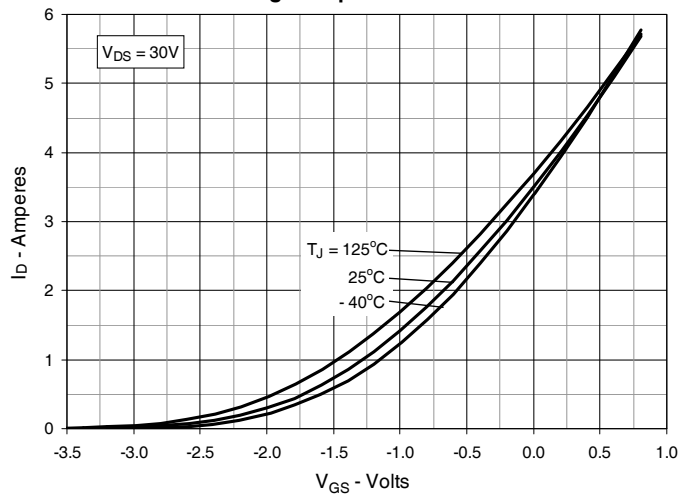


Fig. 10. Transconductance

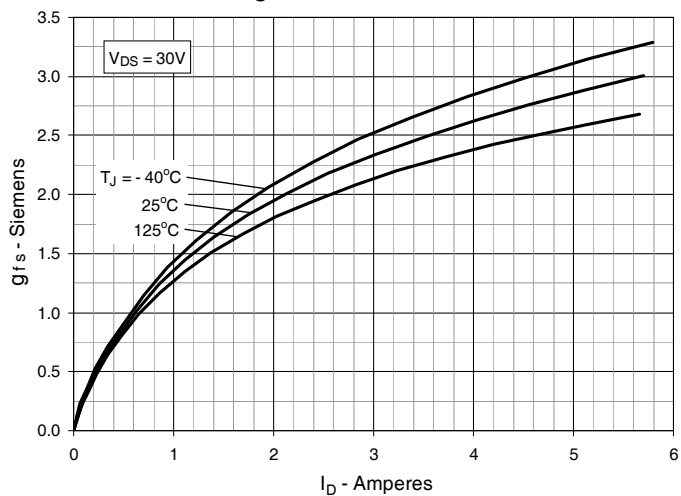


Fig. 11. Breakdown and Threshold Voltages vs. Junction Temperature

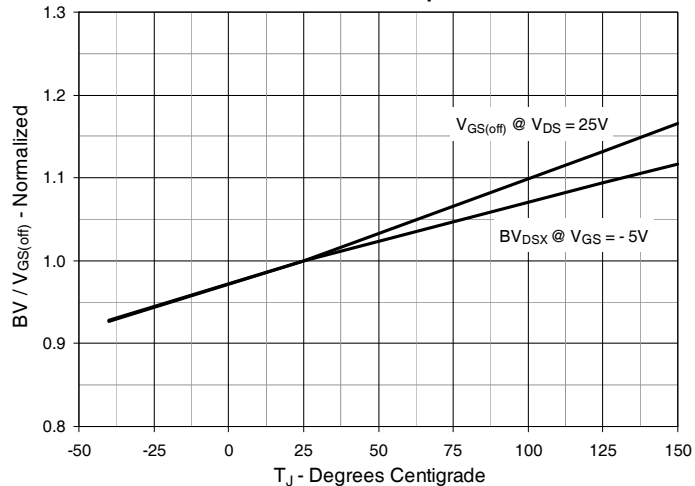


Fig. 12. Forward Voltage Drop of Intrinsic Diode

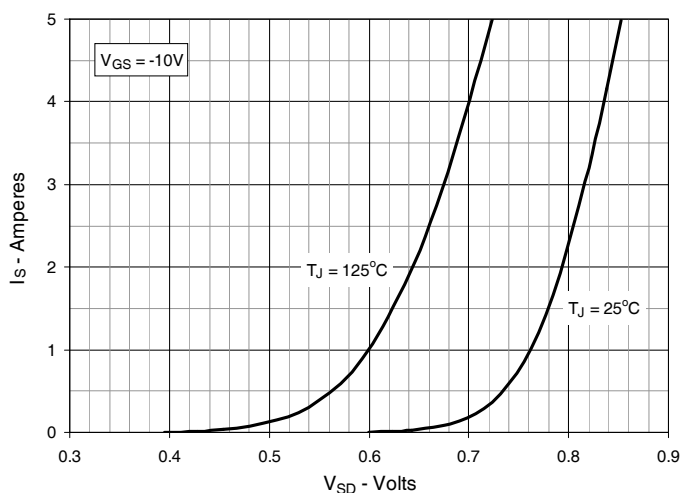


Fig. 13. Capacitance

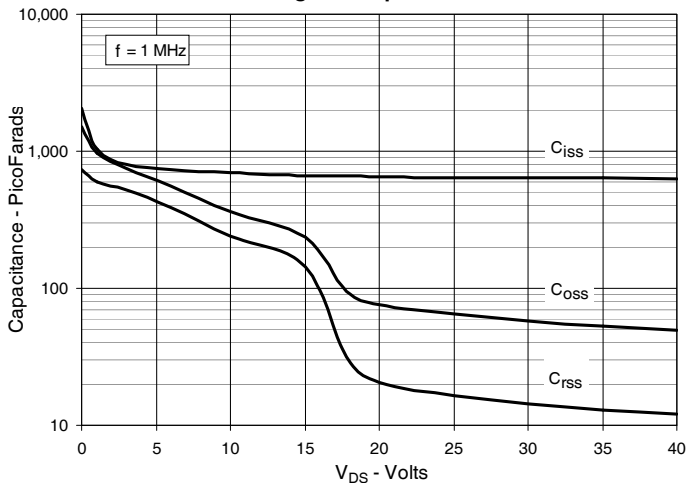


Fig. 14. Gate Charge

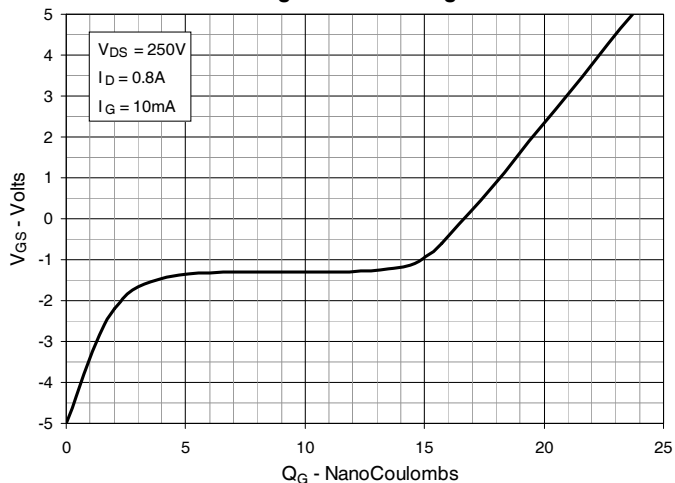


Fig. 15. Forward-Bias Safe Operating Area  
@ T<sub>C</sub> = 25°C

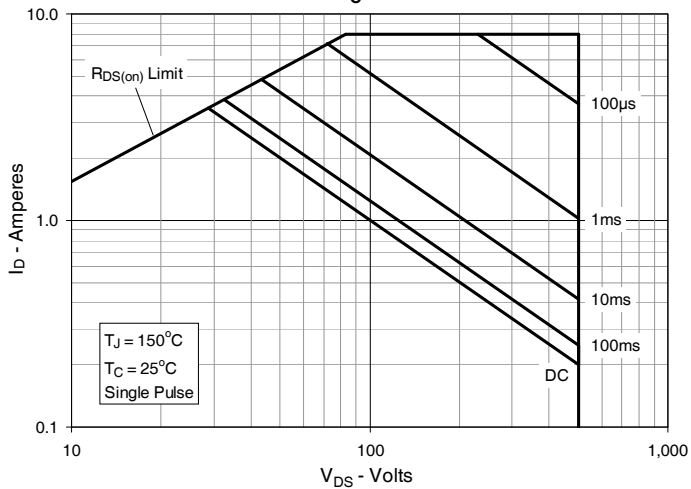


Fig. 16. Forward-Bias Safe Operating Area  
@ T<sub>C</sub> = 75°C

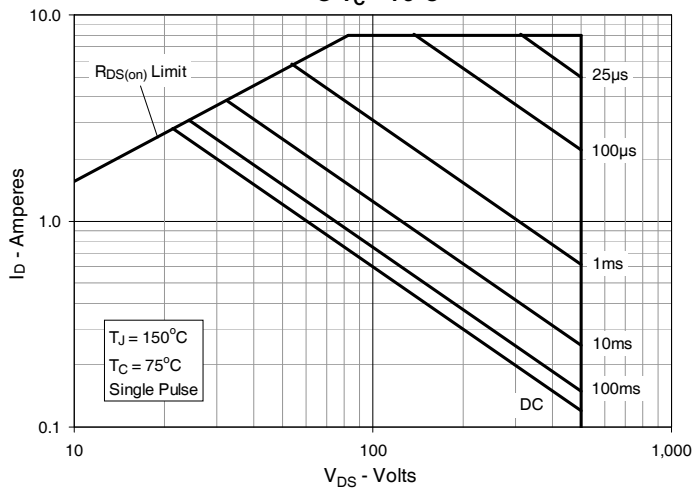
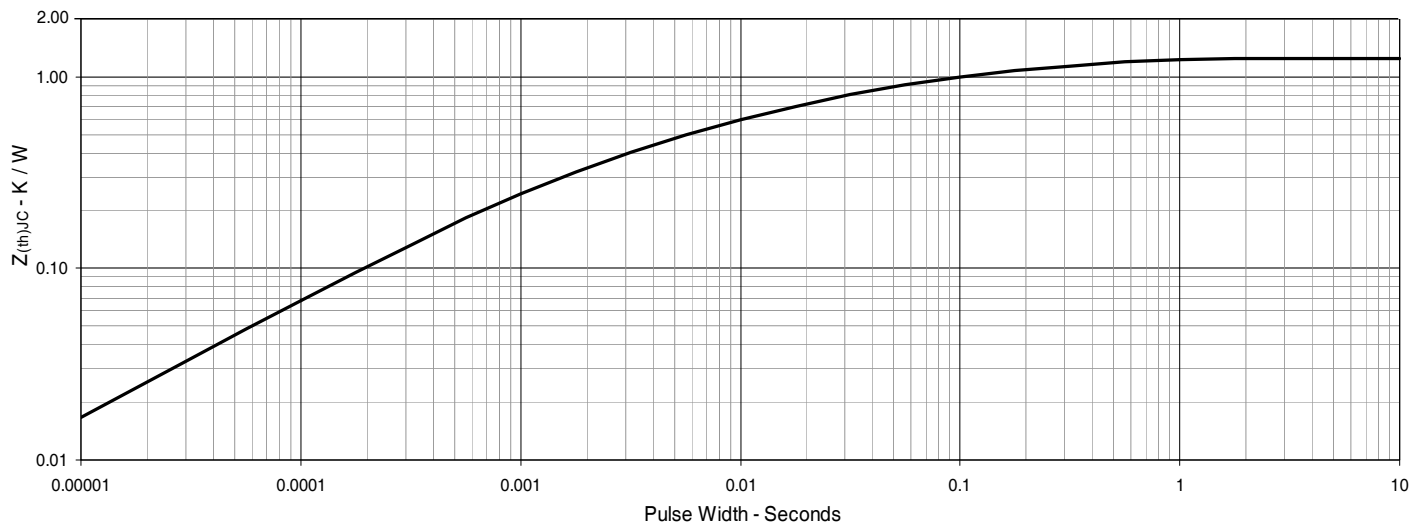
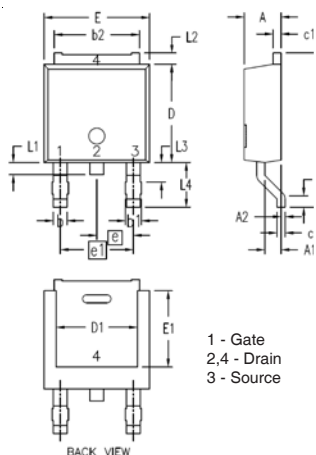


Fig. 17. Maximum Transient Thermal Resistance



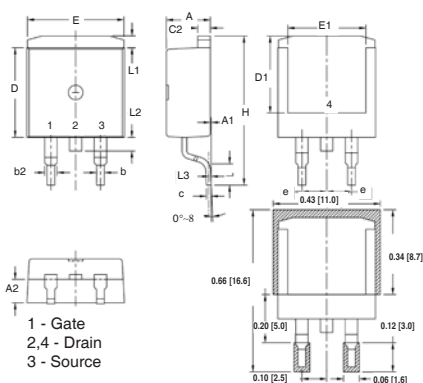
### TO-252 Outline



1 - Gate  
2,4 - Drain  
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.086	.094	2.19	2.38
A1	.035	.045	0.89	1.14
A2	0	.004	0	0.10
b	.025	.035	0.64	0.89
b1	.030	.045	0.76	1.14
b2	.205	.215	5.21	5.46
c	.018	.023	0.46	0.58
c1	.018	.023	0.46	0.58
D	.235	.245	5.97	6.22
D1	.170	.205	4.32	5.21
E	.250	.265	6.35	6.73
E1	.170	.205	4.32	5.21
e	.090 BSC		2.28 BSC	
e1	.180 BSC		4.57 BSC	
H	.370	.410	9.40	10.42
L	.020	.040	0.51	1.02
L1	.025	.040	0.64	1.02
L2	.024	.036	0.60	0.90
L3	.045	.060	1.15	1.52
L4	.100	.115	2.54	2.92

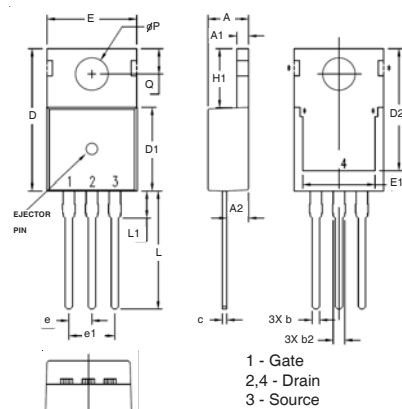
### TO-263 Outline



1 - Gate  
2,4 - Drain  
3 - Source

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.060	1.18	1.52
C	.018	.024	0.45	0.60
C2	.049	.060	1.25	1.52
D	.340	.370	8.63	9.40
D1	.300	.327	7.62	8.30
E	.380	.410	9.65	10.41
E1	.270	.330	6.86	8.38
[e]	.100 BSC		2.54 BSC	
H	.580	.620	14.73	15.75
L	.075	.105	1.91	2.67
L1	.039	.060	1.00	1.52
L2	—	.070	—	1.77
[L3]	.010 BSC		0.254 BSC	

### TO-220 Outline



1 - Gate  
2,4 - Drain  
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100 BSC		2.54 BSC	
e1	.200 BSC		5.08 BSC	
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
∅P	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20



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С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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